Fig. 3
Residual polymers unstripped

OCD35096 — 1 pm MERCK REMAND

Fig. 4 After stripping with 100 ppm of H_2SiF_6

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Fig. 5 After stripping with 500 ppm of H_2SiF_6

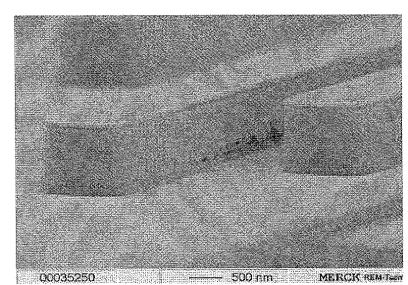


Fig. 6 After stripping with 1000 ppm of H_2SiF_6

10 OCC33090 — 500 nm MERCK REM-THAN

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Fig. 7
After stripping with 100 ppm of HF

90035110 — 500 nm MERCK REMJest

Fig. 8
After stripping with 200 ppm of HF

5 00035106 500 mm MERCK REMIGNATION

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Fig. 9
After stripping with 500 ppm of HF

500 nm MERCK REM Team

Stripping results in a Mattson AWP tank processor with various $H_2 \mathrm{SiF}_6$ concentrations.

Fig. 10
After stripping with 100 ppm of H₂SiF₆

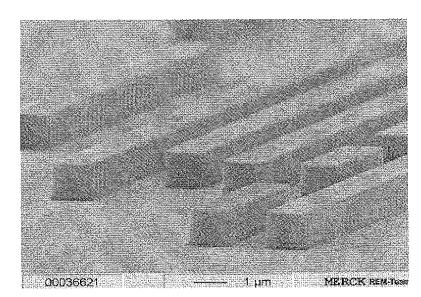
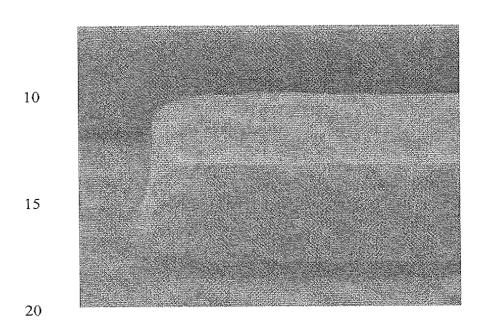


Fig. 11 After stripping with 600 ppm of H_2SiF_6

1 µm MERCK REM-Team

Fig. 12: Result after use of a composition with added surfactant.



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Fig. 13
Comparison with Fig. 12: Result after use of a composition without added surfactant.